JFETs - General Purpose

N-Channel – Depletion

N-Channel Junction Field Effect Transistors, depletion mode (Type A) designed for audio and switching applications.

Features

- N-Channel for Higher Gain
- Drain and Source Interchangeable
- High AC Input Impedance
- High DC Input Resistance
- Low Transfer and Input Capacitance
- Low Cross-Modulation and Intermodulation Distortion
- Plastic Encapsulated Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS

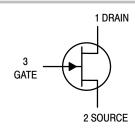
Rating	Symbol	Value	Unit	
Drain-Source Voltage	V _{DS}	25	Vdc	
Drain-Gate Voltage	V _{DG}	25	Vdc	
Reverse Gate – Source Voltage	V _{GSR}	-25	Vdc	
Gate Current	l _G	10	mAdc	
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	310 2.82	mW mW/°C	
Operating Junction Temperature	TJ	135	°C	
Storage Temperature Range	T _{stg}	-65 to +150	°C	

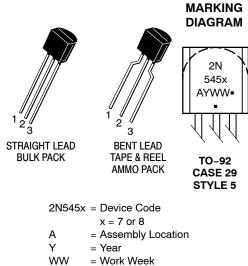
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
2N5457	TO-92	1000 Units/Box
2N5457G	TO-92 (Pb-Free)	1000 Units/Box
2N5458	TO-92	1000 Units/Box
2N5458G	TO-92 (Pb-Free)	1000 Units/Box

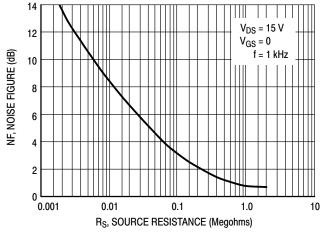
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

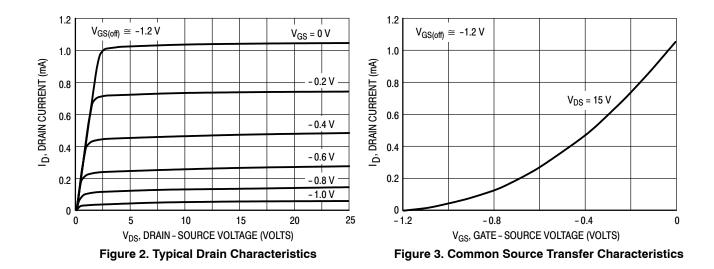
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Gate – Source Breakdown Voltage ($I_G = -10 \ \mu Adc, \ V_{DS} = 0$)		V _{(BR)GSS}	-25	-	_	Vdc
Gate Reverse Current		I _{GSS}		- -	-1.0 -200	nAdc
Gate-Source Cutoff Voltage (V _{DS} = 15 Vdc, i _D = 10 nAdc)	2N5457 2N5458	V _{GS(off)}	-0.5 -1.0	- -	-6.0 -7.0	Vdc
$\label{eq:Gate-Source Voltage} \begin{array}{l} \mbox{Gate-Source Voltage} \\ \mbox{(V}_{DS} = 15 \mbox{ Vdc}, i_D = 100 \mu \mbox{Adc}) \\ \mbox{(V}_{DS} = 15 \mbox{ Vdc}, i_D = 200 \mu \mbox{Adc}) \end{array}$	2N5457 2N5458	V _{GS}		-2.5 -3.5		Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0)$	2N5457 2N5458	I _{DSS}	1.0 2.0	3.0 6.0	5.0 9.0	mAdc
DYNAMIC CHARACTERISTICS				•		•
Forward Transfer Admittance (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$	2N5457 2N5458	Y _{fs}	1000 1500	3000 4000	5000 5500	μmhos
Output Admittance Common Source (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$		Y _{os}	_	10	50	μmhos
Input Capacitance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$		C _{iss}	_	4.5	7.0	pF
Reverse Transfer Capacitance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$		C _{rss}	-	1.5	3.0	pF

1. Pulse Width \leq 630 ms, Duty Cycle \leq 10%.

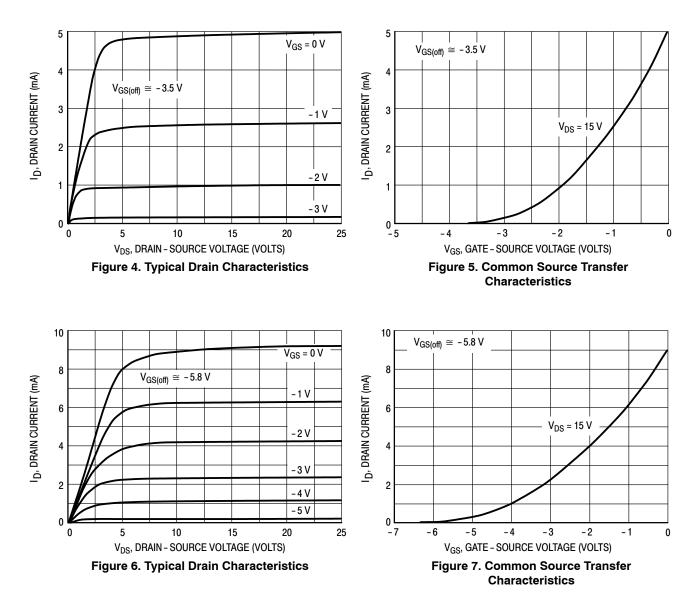








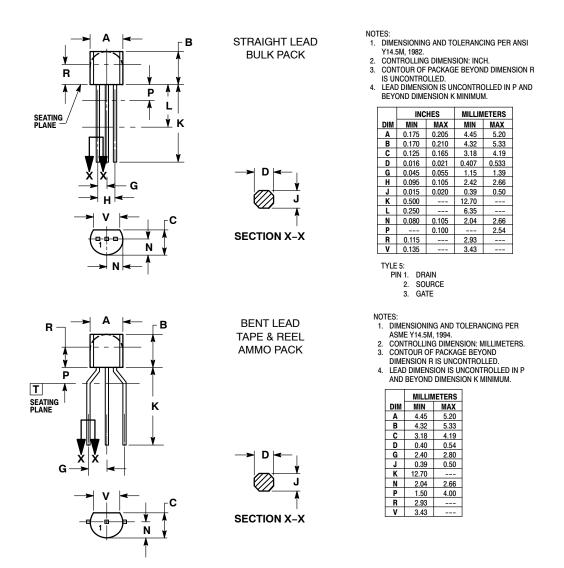
TYPICAL CHARACTERISTICS For 2N5457 Only



NOTE: Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS}.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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